

1SS265

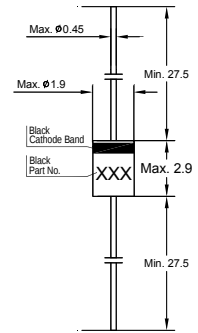
Silicon Epitaxial Planar Switching Diode

Features

- Glass sealed envelope
- High speed
- High reliability

Applications

- High-speed switching



Glass Case DO-34
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	90	V
DC Reverse Voltage	V_R	80	V
Average Rectified Forward Current	$I_{F(AV)}$	130	mA
Peak Forward Current	I_{FM}	400	mA
Surge Forward Current at $t < 1\text{ s}$	I_{FSM}	600	mA
Power Dissipation	P_{tot}	300	mW
Junction Temperature	T_j	175	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 175	$^{\circ}\text{C}$

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$	V_F	1.2	V
Reverse Current at $V_R = 80\text{ V}$	I_R	0.5	μA
Capacitance at $V_R = 0.5\text{ V}$, $f = 1\text{ MHz}$	C_T	1.5	pF
Reverse Recovery Time at $I_F = 10\text{ mA}$, $V_R = 6\text{ V}$, $R_L = 50\text{ }\Omega$	t_{rr}	4	ns

